



## DRV883x 低压 H 桥驱动器

### 1 特性

- H 桥电机驱动器
  - 驱动一个直流电机或其他负载
  - 低金属氧化物半导体场效应晶体管 (MOSFET) 导通电阻: 高侧 + 低侧 (HS + LS) 280mΩ
- 1.8A 最大驱动电流
- 独立的电机和逻辑电源引脚:
  - 电机 VM: 0 至 11V
  - 逻辑 VCC: 1.8 至 7V
- 脉宽调制 (PWM) 或 PH/EN 接口
  - DRV8837: 脉宽调制 (PWM), IN1/IN2
  - DRV8838: PH/EN
- 具有 120nA 最大睡眠电流的低功耗睡眠模式
  - nSLEEP 引脚
- 小型封装尺寸
  - 8 超薄小外形尺寸封装 (WSON) (PowerPAD™)
  - 2.0mm × 2.0mm
- 保护特性
  - VCC 欠压闭锁 (UVLO)
  - 过流保护 (OCP)
  - 热关断 (TSD)

### 2 应用范围

- 摄像机
- 数字单镜头反光 (DSLR) 镜头
- 消费类产品
- 玩具
- 机器人技术
- 医疗设备

### 3 说明

DRV883x 为摄像机、消费类产品、玩具和其它低电压或者电池供电的运动控制类应用提供了一个集成的电机驱动器解决方案。此器件能够驱动一个直流电机或其他诸如螺线管的器件。输出驱动器块由一个配置为 H 桥的 N 通道功率 MOSFET 组成, 以驱动电机绕组。一个内部电荷泵生成所需的栅极驱动电压。

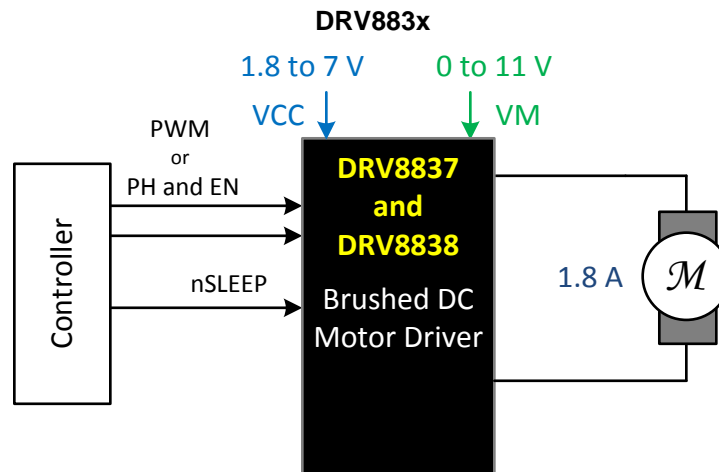
DRV883x 能够提供高达 1.8A 的输出电流。它运行在 0 至 11V 之间的电机电源电压, 以及 1.8V 至 7.0V 范围内的器件电源电压上。

DRV8837 具有一个 PWM (IN/IN) 输入接口; DRV8837 具有一个 PH/EN 输入接口 (此处应为 DRV8838 具有一个 PH/EN 输入接口)。这两个接口都与行业标准器件兼容。

还提供用于过流保护、短路保护、欠压闭锁和过热保护的内部关断功能。

器件信息

订货编号	封装	封装尺寸
DRV8837DSGR	WSON (8)	2.0mm x 2.0mm
DRV8838DSGR	WSON (8)	2.0mm x 2.0mm



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## 4 修订历史记录

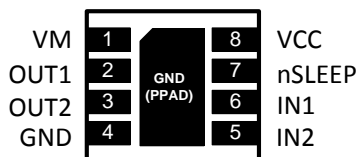
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

<b>Changes from Revision B (December 2013) to Revision C</b>	<b>Page</b>
• 已添加 DRV8838 器件信息、技术规格和时序图 .....	<b>1</b>
• 已添加器件信息表 .....	<b>1</b>
• 已添加一个 PWM 接口图 .....	<b>1</b>
• Added more information to the Detailed Description and moved information from the Functional Description .....	<b>9</b>
• Added functional block diagram for DRV8838 .....	<b>10</b>
• Added the Applications and Implementation section .....	<b>13</b>
• Added Power Supply Recommendations, Layout, Device and Documentation Support, and Packaging sections .....	<b>15</b>

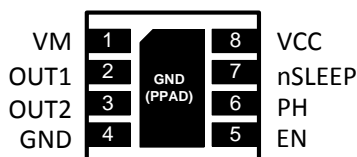
<b>Changes from Revision A (August 2012) to Revision B</b>	<b>Page</b>
• 已更改 特性部分 .....	<b>1</b>
• Changed Recommended Operating Conditions .....	<b>4</b>
• Changed Electrical Characteristics section .....	<b>5</b>
• Changed Timing Requirements section .....	<b>6</b>
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## 5 Terminal Configuration and Functions

**DRV8837 DSG – WSON  
(Top View)**



**DRV8838 DSG – WSON  
(Top View)**



### Terminal Descriptions

TERMINAL		TYPE	DESCRIPTION
NAME	NUMBER		
POWER AND GROUND			
GND	4	PWR	Device ground Must be connected to ground
VCC	8	PWR	Logic Power supply Bypass to GND with a 0.1-μF ceramic capacitor rated for VCC
VM	1	PWR	Motor power supply Bypass to GND with a 0.1-μF ceramic capacitor rated for VM
CONTROL			
IN1/PH	6	I	IN1 or PHASE input See <a href="#">Detailed Description</a> for more information
IN2/EN	5	I	IN2 or ENABLE input
nSLEEP	7	I	Sleep mode input Logic low puts the device in low-power sleep mode; logic high for normal operation; internal pulldown resistor
OUTPUT			
OUT1	2	O	Motor output
OUT2	3	O	Connect to motor winding

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)(2)</sup>

	MIN	MAX	UNIT
Motor power supply voltage range (VM)	–0.3	12	V
Logic power supply voltage range (VCC)	–0.3	7	V
Control pin voltage range (IN1, IN2, PH, EN, nSLEEP)	–0.5	7	V
Peak drive current (OUT1, OUT2)	Internally limited		A
T <sub>J</sub> , operating virtual junction temperature range	–40	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to network ground terminal.

### 6.2 Handling Ratings

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
T <sub>stg</sub> Storage temperature range	–60	150	°C

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

	MIN	MAX	UNIT
VM Motor power supply voltage range	0	11	V
VCC Logic power supply voltage range	1.8	7	V
I <sub>OUT</sub> Motor peak current	0	1.8	A
f <sub>PWM</sub> Externally applied PWM frequency	0	250	kHz
V <sub>LOGIC</sub> Logic level input voltage	0	5.5	V
T <sub>A</sub> Operating ambient temperature	–40	85	°C

- (1) Power dissipation and thermal limits must be observed.

### 6.4 Thermal Information

over operating free-air temperature range (unless otherwise noted)

THERMAL METRIC <sup>(1)</sup>		DRV8837, DRV8838	UNIT
		WSON (8 TERMINALS)	
Θ <sub>JA</sub>	Junction-to-ambient thermal resistance <sup>(2)</sup>	60.9	°C/W
Θ <sub>JC(TOP)</sub>	Junction-to-case (top) thermal resistance <sup>(3)</sup>	71.4	
Θ <sub>JB</sub>	Junction-to-board thermal resistance <sup>(4)</sup>	32.2	
Ψ <sub>JT</sub>	Junction-to-top characterization parameter <sup>(5)</sup>	1.6	
Ψ <sub>JB</sub>	Junction-to-board characterization parameter <sup>(6)</sup>	32.8	
Θ <sub>JC(BOTTOM)</sub>	Junction-to-case (bottom) thermal resistance <sup>(7)</sup>	9.8	

- (1) For more information about traditional and new thermal limits, see the IC Package Thermal Metrics Report, [SPRA953](#).
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter, Ψ<sub>JT</sub>, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining Θ<sub>JA</sub>, using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter, Ψ<sub>JB</sub>, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining Θ<sub>JA</sub>, using a procedure described in JESD51-2a (sections 6 and 7).
- (7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

## 6.5 Electrical Characteristics

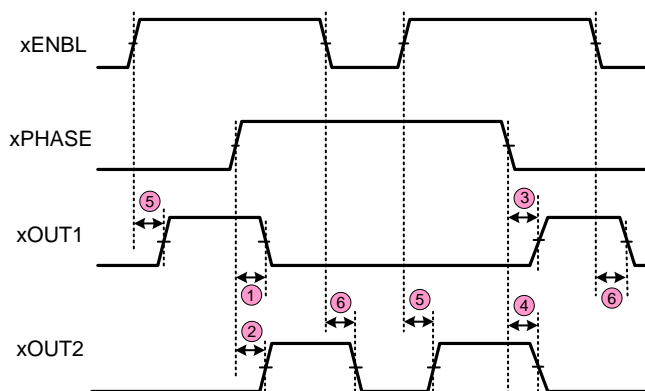
$T_A = 25^\circ\text{C}$ , over recommended operating conditions unless otherwise noted

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER SUPPLIES (VM, VCC)						
VM	VM operating voltage		0		11	V
I <sub>VM</sub>	VM operating supply current	VM = 5 V; VCC = 3 V; No PWM		40	100	μA
		VM = 5 V; VCC = 3 V; 50 kHz PWM		0.8	1.5	mA
I <sub>VMQ</sub>	VM sleep mode supply current	VM = 5 V; VCC = 3 V; nSLEEP = 0		30	95	nA
VCC	VCC operating voltage		1.8		7	V
I <sub>VCC</sub>	VCC operating supply current	VM = 5 V; VCC = 3 V; No PWM		300	500	μA
		VM = 5 V; VCC = 3 V; 50 kHz PWM		0.7	1.5	mA
I <sub>VCCQ</sub>	VCC sleep mode supply current	VM = 5 V; VCC = 3 V; nSLEEP = 0		5	25	nA
CONTROL INPUTS (IN1/PH, IN2/EN, nSLEEP)						
V <sub>IL</sub>	Input logic low voltage		0.25 × VCC	0.38 × VCC		V
V <sub>IH</sub>	Input logic high voltage		0.46 × VCC	0.5 × VCC		V
V <sub>HYS</sub>	Input logic hysteresis		0.08 × VCC			mV
I <sub>IL</sub>	Input logic low current	V <sub>IN</sub> = 0 V	−5		5	μA
I <sub>IH</sub>	Input logic high current	V <sub>IN</sub> = 3.3 V			50	μA
		V <sub>IN</sub> = 3.3 V, DRV8838 nSLEEP pin		60		μA
R <sub>PD</sub>	Pulldown resistance			100		kΩ
		DRV8838 nSLEEP pin		55		kΩ
MOTOR DRIVER OUTPUTS (OUT1, OUT2)						
R <sub>DS(ON)</sub>	HS + LS FET on-resistance	VM = 5 V; VCC = 3 V; I <sub>O</sub> = 800 mA; T <sub>J</sub> = 25°C		280	330	mΩ
I <sub>OFF</sub>	Off-state leakage current	V <sub>OUT</sub> = 0 V	−200		200	nA
PROTECTION CIRCUITS						
V <sub>UVLO</sub>	VCC undervoltage lockout	VCC falling			1.7	V
		VCC rising			1.8	
I <sub>OCP</sub>	Overcurrent protection trip level		1.9		3.5	A
t <sub>DEG</sub>	Overcurrent deglitch time			1		μs
t <sub>RETRY</sub>	Overcurrent retry time			1		ms
T <sub>TSD</sub>	Thermal shutdown temperature	Die temperature T <sub>J</sub>	150	160	180	°C

## 6.6 Timing Requirements

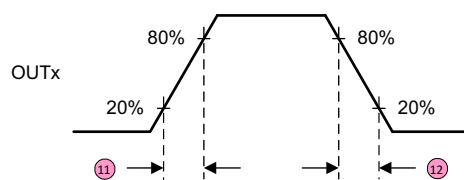
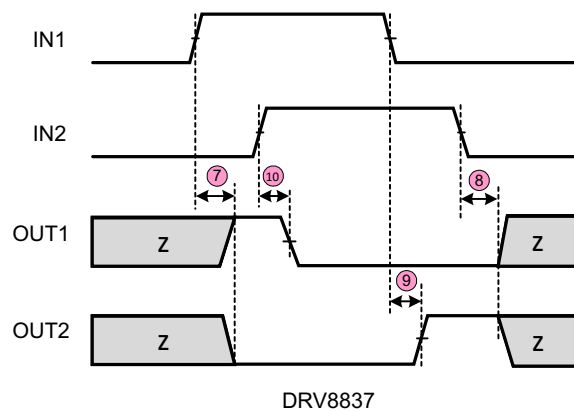
$T_A = 25^\circ\text{C}$ ,  $V_M = 5\text{ V}$ ,  $V_{CC} = 3\text{ V}$ ,  $R_L = 20\ \Omega$

NUMBER	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT
1	$t_1$	Delay time, PHASE high to OUT1 low		160	ns
2	$t_2$	Delay time, PHASE high to OUT2 low		200	ns
3	$t_3$	Delay time, PHASE low to OUT1 high		200	ns
4	$t_4$	Delay time, PHASE low to OUT2 low		160	ns
5	$t_5$	Delay time, ENBL high to OUTx high		200	ns
6	$t_6$	Delay time, ENBL low to OUTx low		160	ns
7	$t_7$	Output enable time		300	ns
8	$t_8$	Output disable time		300	ns
9	$t_9$	Delay time, INx high to OUTx high		160	ns
10	$t_{10}$	Delay time, INx low to OUTx low		160	ns
11	$t_{11}$	Output rise time	30	188	ns
12	$t_{12}$	Output fall time	30	188	ns
	$t_{\text{wake}}$	Wake time, nSLEEP rising edge to part active		30	$\mu\text{s}$



DRV8838

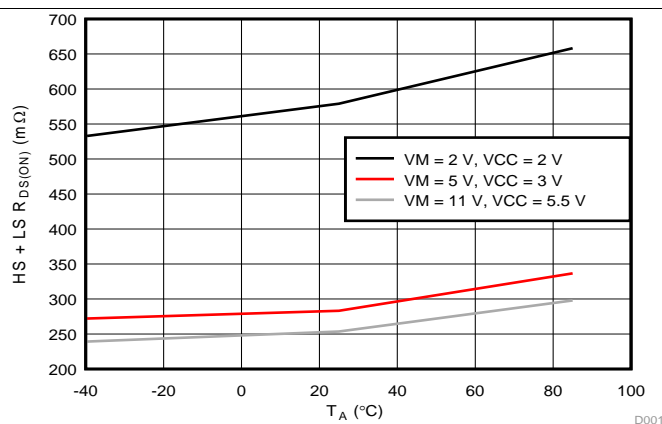
**Figure 1. Input and Output Timing for DRV8838**



**Figure 2. Input and Output Timing for DRV8837**

## 6.7 Typical Characteristics

Plot generated using characterization data



**Figure 3. HS + LS  $R_{DS(ON)}$  vs  $T_A$**



## 7 Detailed Description

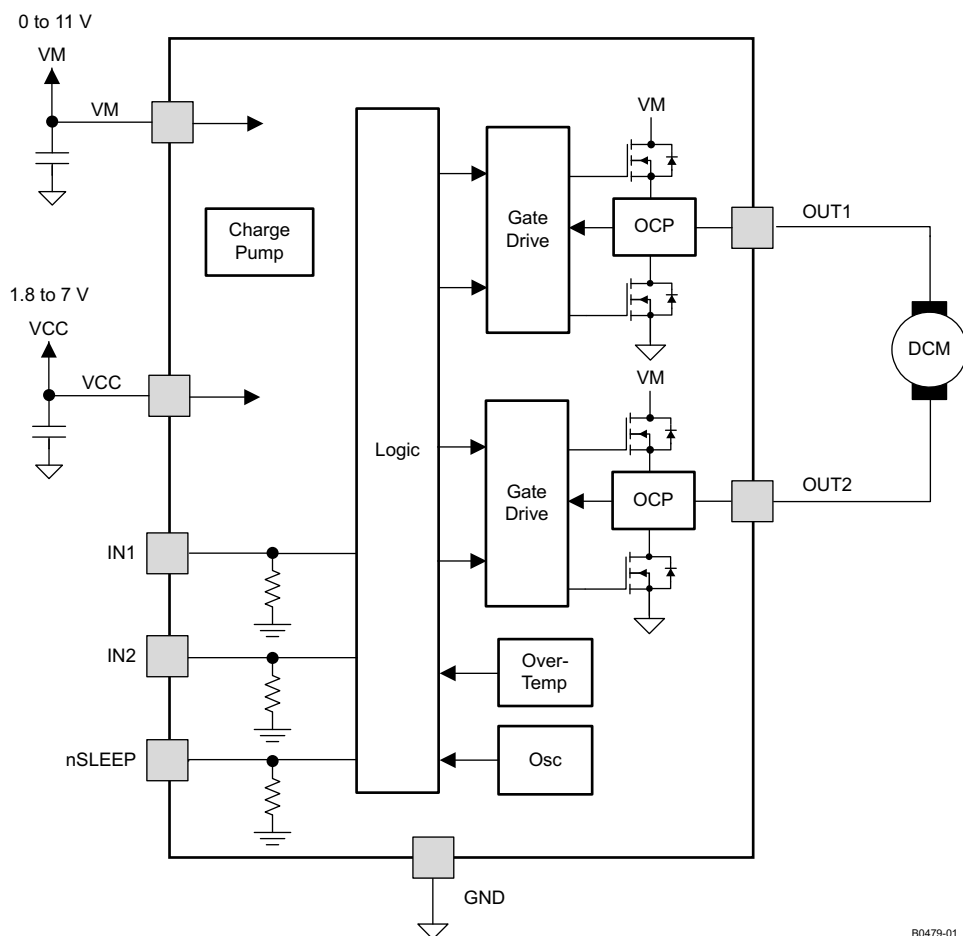
### 7.1 Overview

The DRV883x is a H-bridge driver that can drive one DC motor or other devices like solenoids. The outputs are controlled using either a PWM interface (IN1/IN2) on the DRV8837 or a PH/EN interface on the DRV8838.

A low-power sleep mode is included, which can be enabled using the nSLEEP pin.

These devices greatly reduce the component count of motor driver systems by integrating the necessary driver FETs and FET control circuitry into a single device. In addition, the DRV883x adds protection features above traditional discrete implementations: undervoltage lockout, overcurrent protection, and thermal shutdown.

### 7.2 Functional Block Diagram



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Figure 4. DRV8837 Functional Block Diagram

## Functional Block Diagram (continued)

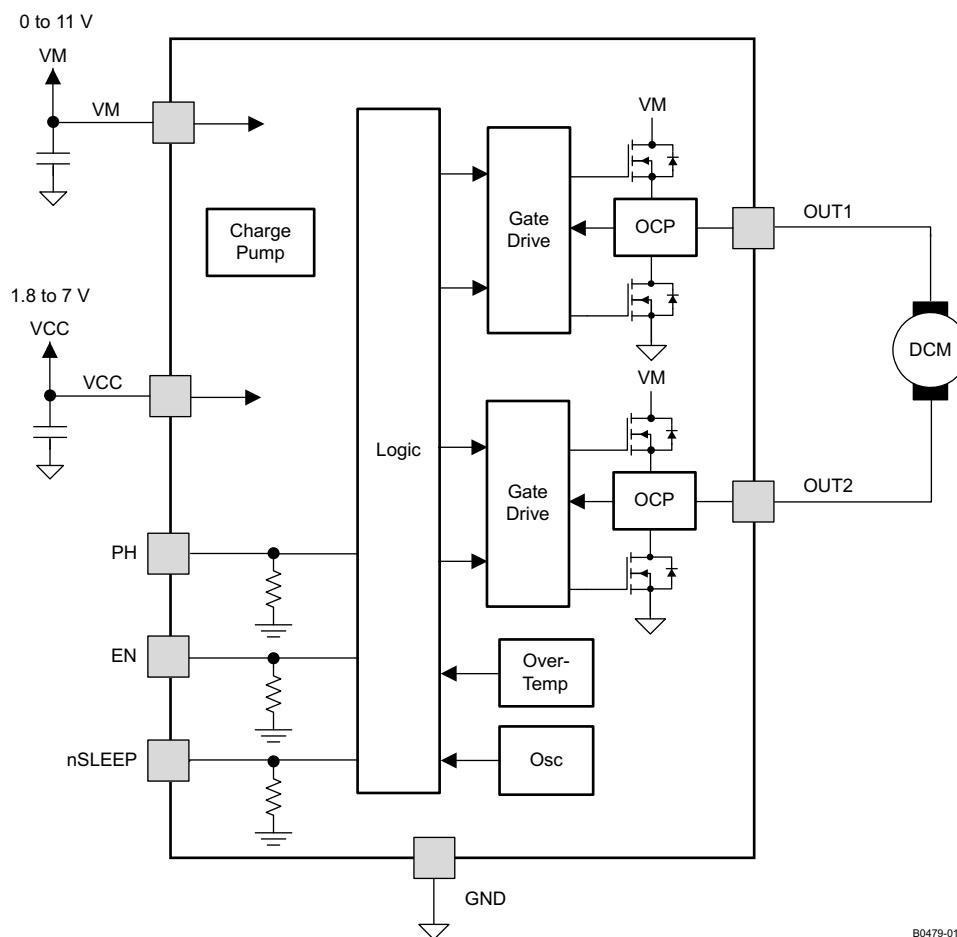


Figure 5. DRV8838 Functional Block Diagram

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## 7.3 Feature Description

### 7.3.1 Bridge Control

The DRV8837 is controlled using a PWM input interface, also called an IN/IN interface. Each output is controlled by a corresponding input pin.

Table 1 shows the logic for the DRV8837 device:

**Table 1. DRV8837 Device Logic**

nSLEEP	IN1	IN2	OUT1	OUT2	Function (DC Motor)
0	X	X	Z	Z	Coast
1	0	0	Z	Z	Coast
1	0	1	L	H	Reverse
1	1	0	H	L	Forward
1	1	1	L	L	Brake

The DRV8838 is controlled using a PHASE/ENABLE interface. This interface uses one pin to control the H-bridge current direction, and one pin to enable or disable the H-bridge.

Table 2 shows the logic for the DRV8838:

**Table 2. DRV8838 Device Logic**

nSLEEP	PH	EN	OUT1	OUT2	Function (DC Motor)
0	X	X	Z	Z	Coast
1	X	0	L	L	Brake
1	1	1	L	H	Reverse
1	0	1	H	L	Forward

### 7.3.2 Sleep Mode

If the nSLEEP pin is brought to a logic-low state, the DRV883x enters a low-power sleep mode. In this state, all unnecessary internal circuitry is powered down.

### 7.3.3 Power Supplies and Input Terminals

The input pins may be driven within their recommended operating conditions with or without the VCC and/or VM power supplies present. No leakage current path will exist to the supply. There is a weak pulldown resistor (approximately 100 k $\Omega$ ) to ground on each input pin.

VCC and VM may be applied and removed in any order. When VCC is removed, the device will enter a low power state and draw very little current from VM. VCC and VM may be connected together if the supply voltage is between 1.8 and 7 V.

The VM voltage supply does not have any undervoltage lockout protection (UVLO), so as long as VCC > 1.8 V; the internal device logic will remain active. This means that the VM pin voltage may drop to 0 V, however, the load may not be sufficiently driven at low VM voltages.

### 7.3.4 Protection Circuits

The DRV883x is fully protected against VCC undervoltage, overcurrent, and overtemperature events.

**VCC Undervoltage Lockout:** If at any time the voltage on the VCC pin falls below the undervoltage lockout threshold voltage, all FETs in the H-bridge will be disabled. Operation resumes when VCC rises above the UVLO threshold.

**Overcurrent Protection (OCP):** An analog current limit circuit on each FET limits the current through the FET by removing the gate drive. If this analog current limit persists for longer than t<sub>DEG</sub>, all FETs in the H-bridge will be disabled. Operation resumes automatically after t<sub>RETRY</sub> has elapsed. Overcurrent conditions will be detected on both the high-side and low-side devices. A short to VM, GND, or from OUT1 to OUT2 results in an overcurrent condition

**Thermal Shutdown (TSD):** If the die temperature exceeds safe limits, all FETs in the H-bridge will be disabled. After the die temperature falls to a safe level, operation automatically resumes.

**Table 3. Fault Behavior**

Fault	Condition	H-bridge	Recovery
VCC undervoltage (UVLO)	$VCC < 1.7\text{ V}$	Disabled	$VCC > 1.8\text{ V}$
Overcurrent (OCP)	$I_{OUT} > 1.9\text{ A (MIN)}$	Disabled	$t_{RETRY}$ elapses
Thermal Shutdown (TSD)	$T_J > 150^\circ\text{C (MIN)}$	Disabled	$T_J < 150^\circ\text{C}$

## 7.4 Device Functional Modes

The DRV883x is active unless the nSLEEP pin is brought logic low. In sleep mode the H-bridge FETs are disabled Hi-Z. The DRV883x is brought out of sleep mode automatically if nSLEEP is brought logic high.

The H-bridge outputs are disabled during undervoltage lockout, overcurrent, and overtemperature fault conditions.

**Table 4. Operation Modes**

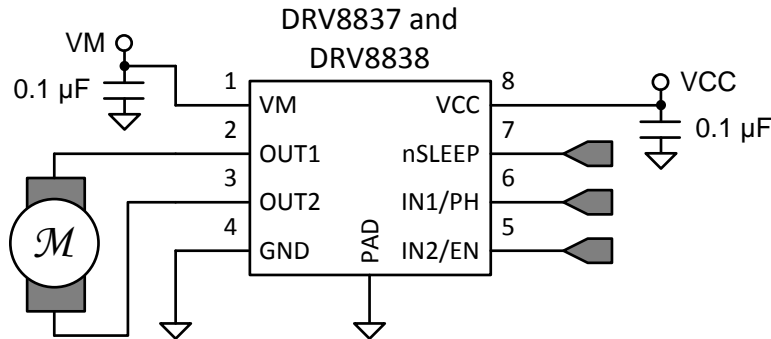
Mode	Condition	H-bridge
Operating	nSLEEP pin = 1	Operating
Sleep mode	nSLEEP pin = 0	Disabled
Fault encountered	Any fault condition met	Disabled

## 8 Applications and Implementation

### 8.1 Application Information

The DRV883x device is used to drive one DC motor or other devices like solenoids. The following design procedure can be used to configure the DRV883x.

### 8.2 Typical Applications



**Figure 6. Schematic of DRV883x Application**

#### 8.2.1 Design Requirements

Table 5 shows required parameters for a typical usage case.

**Table 5. System Design Requirements**

Design Parameter	Reference	Example Value
Motor supply voltage	VM	9 V
Logic supply voltage	VCC	3.3 V
Target RMS current	I <sub>OUT</sub>	0.8 A

#### 8.2.2 Detailed Design Procedure

##### 8.2.2.1 Power Dissipation

Power dissipation in the DRV883x is dominated by the power dissipated in the output FET resistance, or  $R_{DS(ON)}$ . Average power dissipation when running a stepper motor can be roughly estimated by:

$$P_{TOT} = R_{DS(ON)} \times (I_{OUT(RMS)})^2$$

where

- $P_{TOT}$  is the total power dissipation
- $R_{DS(ON)}$  is the resistance of the HS plus LS FETs
- $I_{OUT(RMS)}$  is the RMS or DC output current being supplied to the load

The maximum amount of power that can be dissipated in the device is dependent on ambient temperature and heatsinking.

Note that  $R_{DS(ON)}$  increases with temperature, so as the device heats, the power dissipation increases.

The DRV883x has thermal shutdown protection. If the die temperature exceeds approximately 150°C, the device will be disabled until the temperature drops to a safe level.

Any tendency of the device to enter thermal shutdown is an indication of either excessive power dissipation, insufficient heatsinking, or too high an ambient temperature.

### 8.2.3 Application Performance Plots

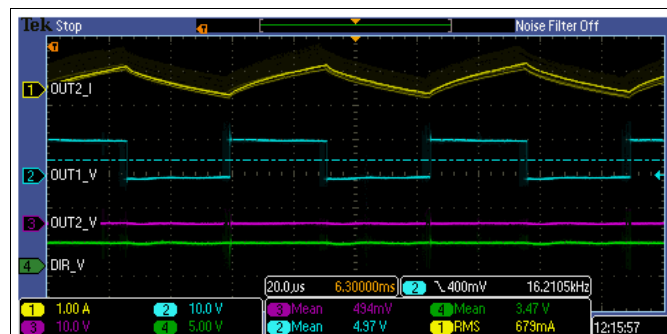


Figure 7. 50% Duty Cycle, Forward Direction

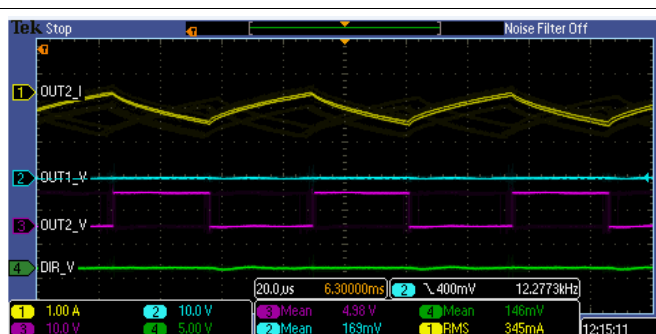


Figure 8. 50% Duty Cycle, Reverse Direction

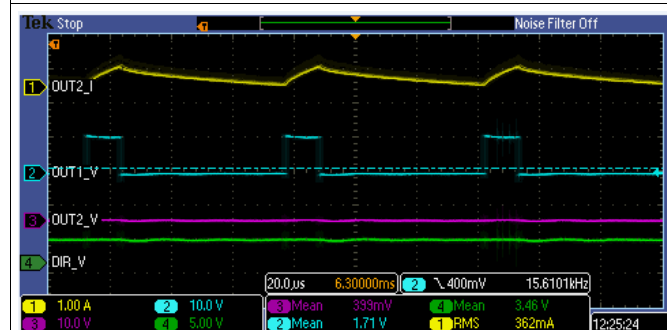


Figure 9. 20% Duty Cycle, Forward Direction

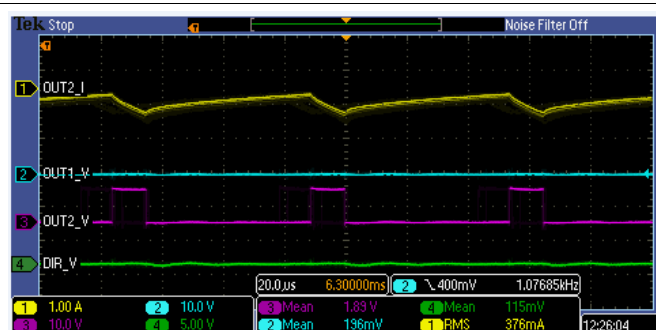


Figure 10. 20% Duty Cycle, Reverse Direction

## 9 Power Supply Recommendations

VCC and VM may be applied and removed in any order. When VCC is removed, the device enters a low power state and draws very little current from VM. VCC and VM may be connected together if the supply voltage is between 1.8 and 7 V.

Bypass VM and VCC with 0.1- $\mu$ F ceramic capacitors rated for VM and VCC. Place these capacitors as close to the device as possible.

The VM voltage supply does not have any undervoltage lockout protection, so as long as  $VCC > 1.8\text{ V}$ ; the internal device logic will remain active. This means that the VM pin voltage may drop to 0 V; however, the load may not be sufficiently driven at low VM voltages.

## 10 Layout

### 10.1 Layout Guidelines

The VM and VCC terminals should be bypassed to GND using low-ESR ceramic bypass capacitors with a recommended value of 0.1  $\mu\text{F}$  rated for VM and VCC. These capacitors should be placed as close to the VM and VCC pins as possible with a thick trace or ground plane connection to the device GND pin.

### 10.2 Layout Example

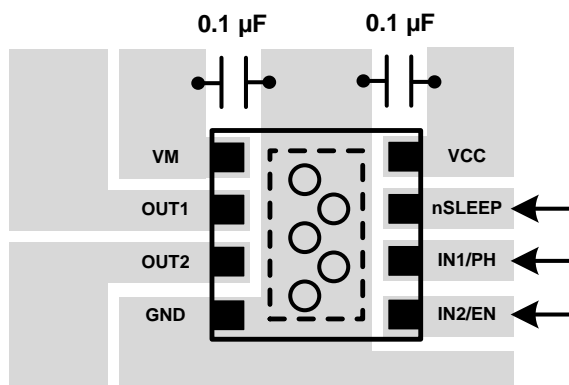


Figure 11. Simplified Layout Example



## 11 Device and Documentation Support

### 11.1 Related Links

The following table lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

**Table 6. Related Links**

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
DRV8837	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>
DRV8838	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>

### 11.2 Trademarks

PowerPAD is a trademark of Texas Instruments.

### 11.3 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 11.4 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms and definitions.

## 12 机械封装和可订购信息

以下页中包括机械封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 要获得这份数据表的浏览器版本，请查阅左侧导航栏。

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DRV8837DSGR	ACTIVE	WSO	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	837	<a href="#">Samples</a>
DRV8837DSGT	ACTIVE	WSO	DSG	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	837	<a href="#">Samples</a>
DRV8838DSGR	ACTIVE	WSO	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	838	<a href="#">Samples</a>
DRV8838DSGT	ACTIVE	WSO	DSG	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	838	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

## TAPE AND REEL INFORMATION



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV8837DSGR	WSN	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
DRV8837DSGR	WSN	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
DRV8837DSGT	WSN	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
DRV8837DSGT	WSN	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
DRV8838DSGR	WSN	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
DRV8838DSGT	WSN	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV8837DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
DRV8837DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
DRV8837DSGT	WSON	DSG	8	250	210.0	185.0	35.0
DRV8837DSGT	WSON	DSG	8	250	210.0	185.0	35.0
DRV8838DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
DRV8838DSGT	WSON	DSG	8	250	210.0	185.0	35.0

## GENERIC PACKAGE VIEW

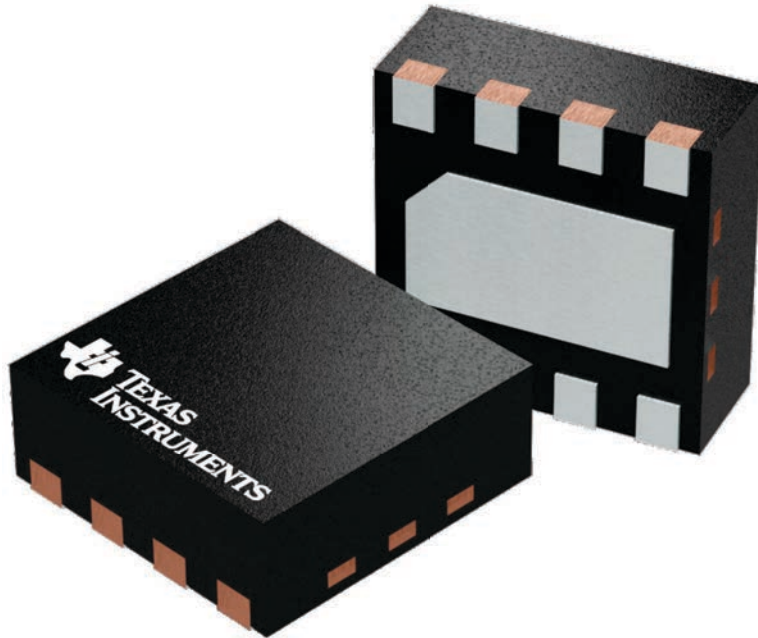
**DSG 8**

**WSON - 0.8 mm max height**

2 x 2, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



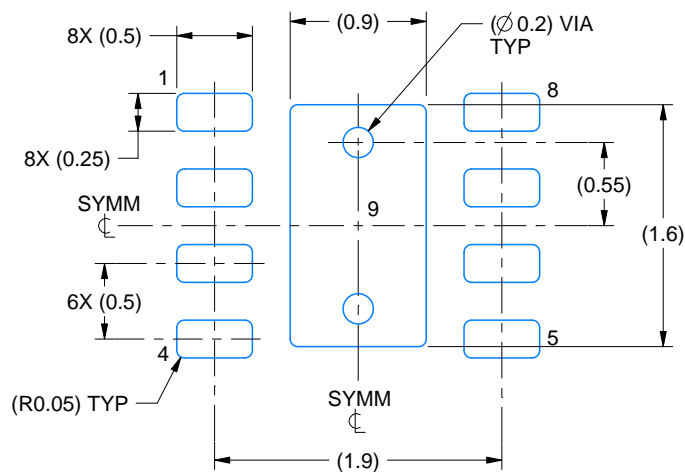




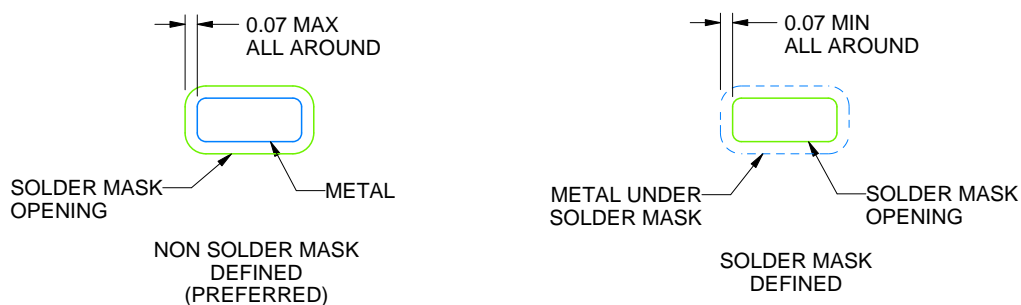
**DSG0008A**

**WSON - 0.8 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE  
SCALE:20X



## SOLDER MASK DETAILS

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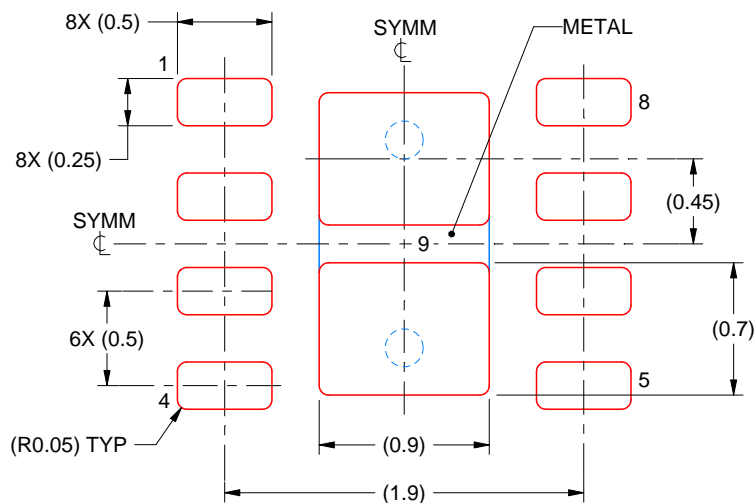
NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/slue271](http://www.ti.com/lit/slue271)).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

**DSG0008A**

**WSON - 0.8 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



## SOLDER PASTE EXAMPLE BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 9:  
87% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE  
SCALE:25X

4218900/D 04/2020

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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